



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: John T. Moore and David L. Chapek § Group Art Unit: 2811
Serial No.: 09/496,794 § Examiner: D. Ov
Filed: February 2, 2000 §
For: Trench Isolation for Semiconductor Devices § Atty. Dkt. No.: MICT

Commissioner for Patents
Washington DC 20231

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RESPONSE TO OFFICE ACTION DATED JUNE 29, 2001

Sir:

In response to the Office Action mailed June 29, 2001, the Applicants make the following amendments and remarks.

In the Claims

Please amend the claims as follows:

Sub C2) 31. (Amended) A semiconductor structure having a trench, comprising:

2 a trench filler material that fills the trench;

3 at least a portion of a second material deposited on the trench filler

4 material and the structure;

5 wherein the second material is annealed; and

6 wherein the etch rate of the second material is substantially similar

7 to or less than the etch rate of the first material.

Please cancel claim 32.

Date of Deposit: 7/31/01
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Sharon V. Hart